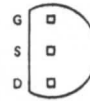
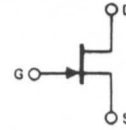


# n-channel JFETs

## J210 J211 J212

### ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate-Source Voltage	.....	-25 V
Gate Current	.....	10 mA
Total Device Dissipation at 25°C Ambient (Derate 3.27 mW/°C)	.....	360 mW
Operating Temperature Range	.....	-55 to 135°C
Storage Temperature Range	.....	-55 to 150°C
Lead Temperature Range (1/16" from case for 10 seconds)	.....	300°C



Bottom View

Plastic



### ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

1	S	Characteristic	J210			J211			J212			Unit	Test Conditions
			Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
2	T	I <sub>GSS</sub> Gate Reverse Current (Note 1)			-100			-100			-100	pA	V <sub>DS</sub> = 0, V <sub>GS</sub> = -15 V
3	A	V <sub>GS(off)</sub> Gate-Source Cutoff Voltage	-1		-3	-2.5		-4.5	-4		-6	V	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1 nA
4	T	BV <sub>GSS</sub> Gate-Source Breakdown Voltage	-25			-25			-25				V <sub>DS</sub> = 0, I <sub>G</sub> = -1 μA
5	I	I <sub>DSS</sub> Saturation Drain Current (Note 2)	2		15	7		20	15		40	mA	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0
6	C	I <sub>G</sub> Gate Current (Note 1)		-10			-10			-10		pA	V <sub>DG</sub> = 10 V, I <sub>D</sub> = 1 mA
7	D	g <sub>fs</sub> Common-Source Forward Transconductance (Note 2)	4,000		12,000	6,000		12,000	7,000		12,000	μmho	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0
8		g <sub>os</sub> Common-Source Output Conductance			150			200			200		
9	M	C <sub>iss</sub> Common-Source Input Capacitance		4			4			4		pF	f = 1 MHz
10		C <sub>rss</sub> Common-Source Reverse Transfer Capacitance		1			1			1			
	C	e <sub>n</sub> Equivalent Short-Circuit Input Noise Voltage		10			10			10		nV/√Hz	f = 1 kHz

